

Broadband polarization-independent antireflection coatings for solar cells from Mie resonators in silicon metasurfaces

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Outline

- About MTI
- The Problem
- metaSolar
- Semiconductor AR Coatings
- Manufacturing

About MTI



PLEASANTON, CA
Rolling Mask Lithography Center

HALIFAX, NS
MTI head office

LONDON, UK
R&D and EU Sales Office

Founded in 2010
35 People
20 Patent Families
metamaterial.com



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TEXAS
 — AT AUSTIN —



ITMO UNIVERSITY

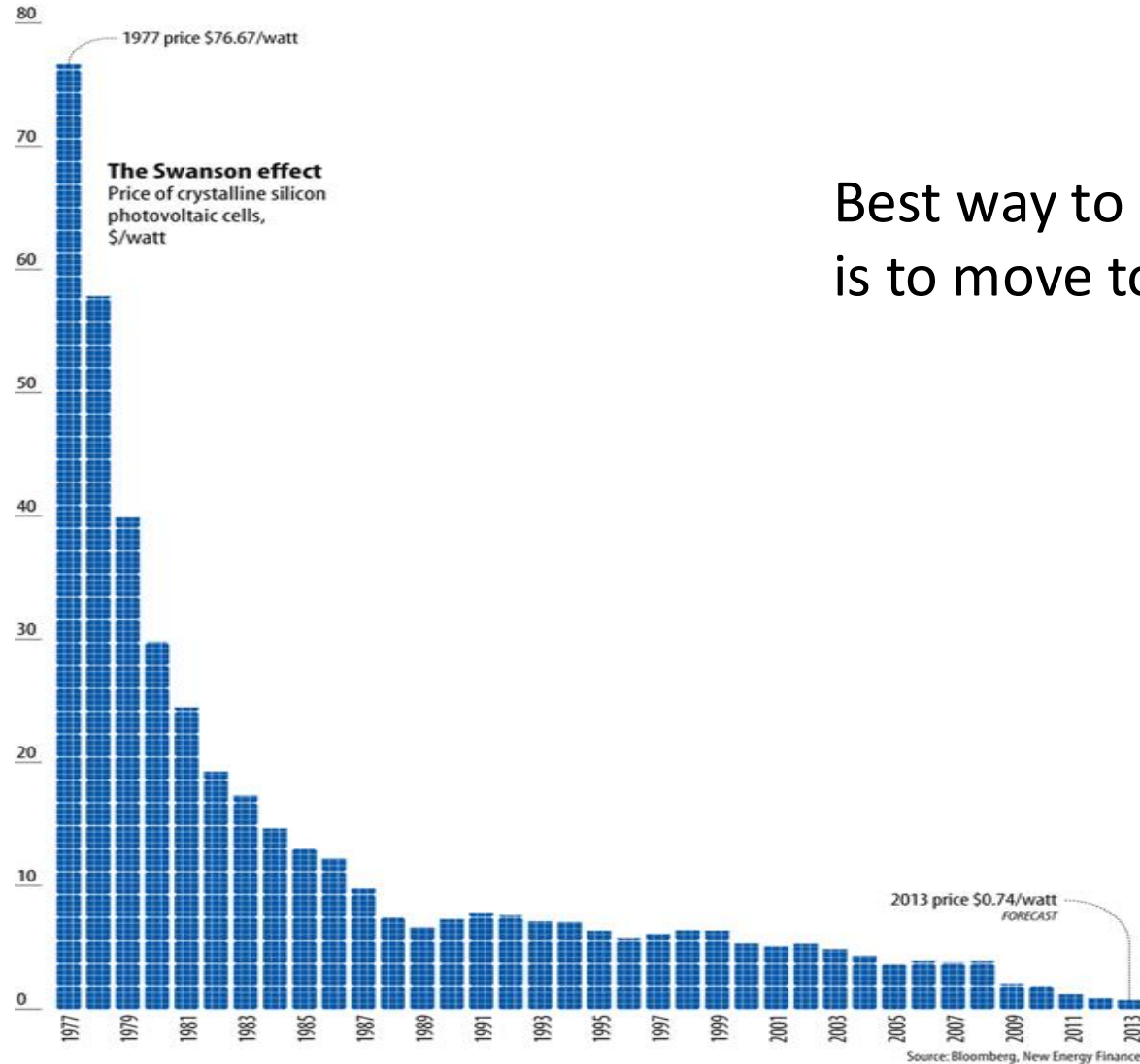




**Metamaterial
Technologies
Inc.**

The Problem

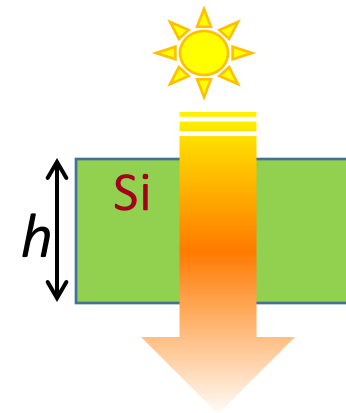
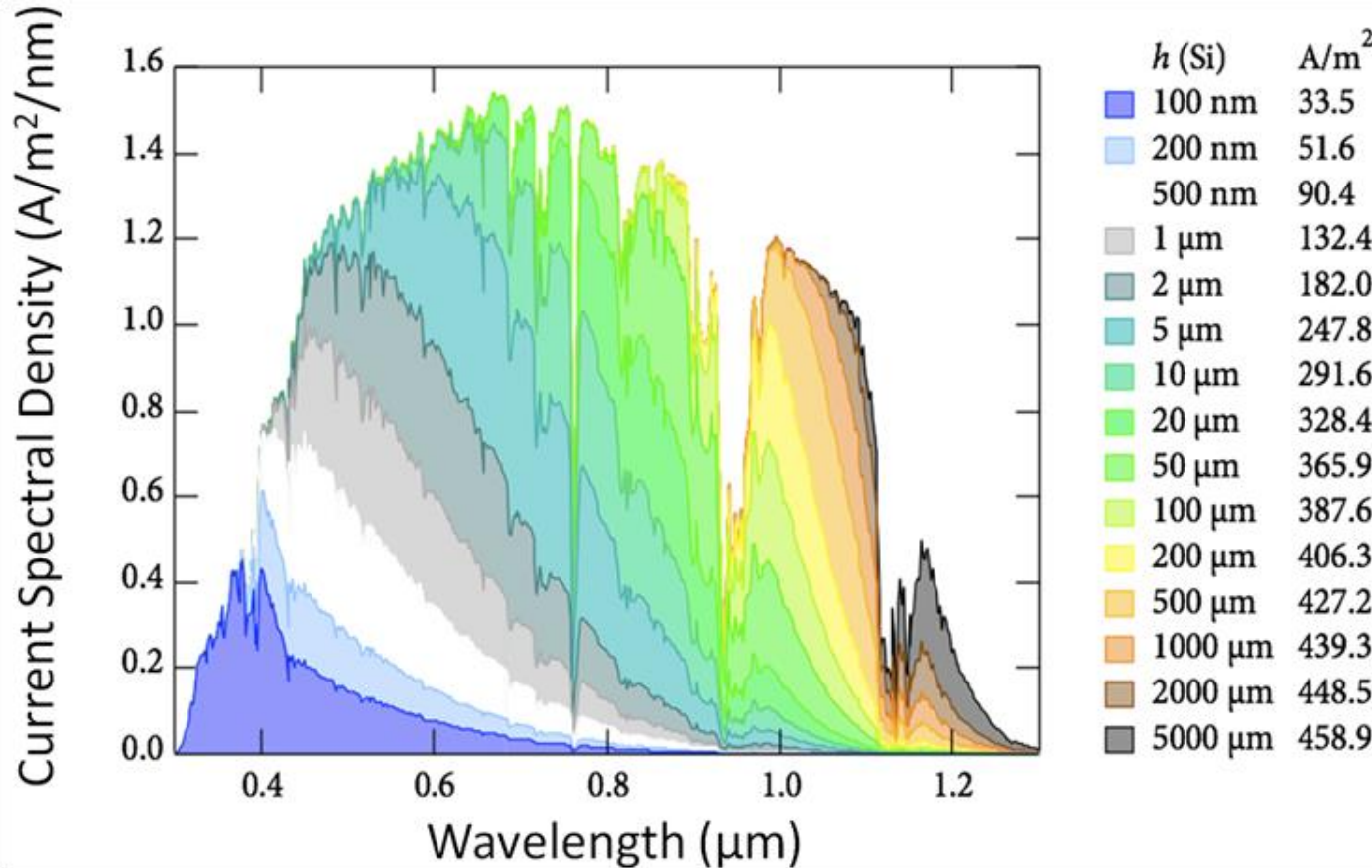
Motivation



Best way to keep reducing price of cSi is to move to thinner, more efficient cells.

Thin Cells: Limited Single Pass Absorption

Example: Single-pass absorption of light in a Si wafer illuminated with the AM 1.5 solar spectrum



- Fraction of absorbed sunlight rapidly decreases with decreasing thickness
- We need very good light trapping layers to enhance the absorption of sunlight per unit volume

ARTICLE

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All-back-contact ultra-thin silicon nanocone solar cells with 13.7% power conversion efficiency

Sangmoo Jeong¹, Michael D. McGehee² & Yi Cui^{2,3}

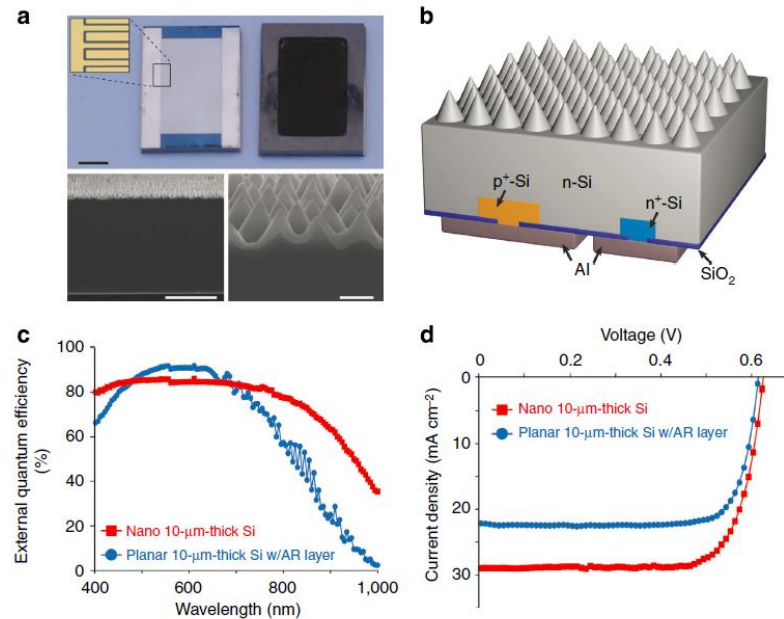
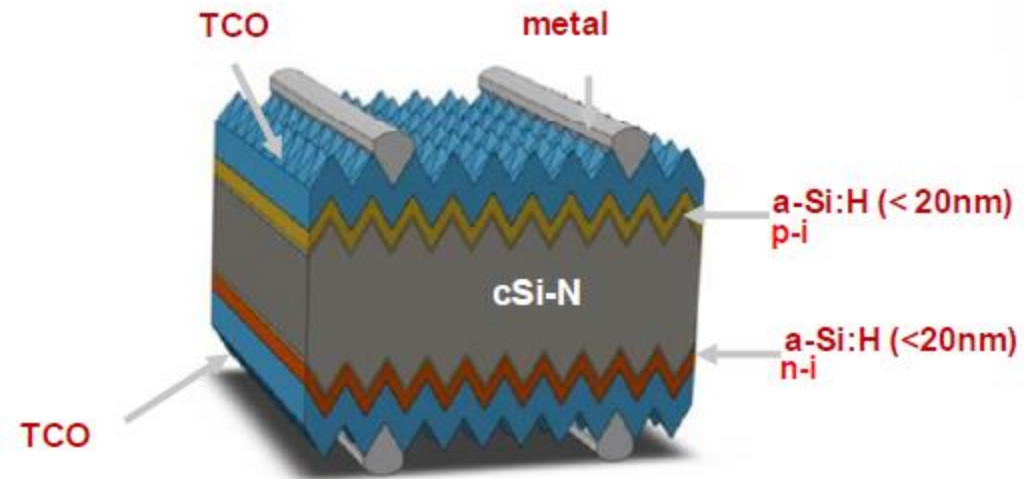


Figure 1 | Ultra-thin Si nanocone solar cell. (a) Optical image of the back (top, left) and front (top, right) side of the 10- μm -thick Si solar cell. Inset shows the optical microscope image of the interdigitated metal electrodes. SEM images of cross-sectional view of the device (bottom, left) and cross-sectional view of the nanocones (bottom, right). The thin layer at the top of the nanocones is an 80-nm-thick SiO₂ layer. Scale bars are 2 mm (top), 5 μm (bottom, left) and 400 nm (bottom, right). (b) Schematic illustration of the device. (c) EQE data of the device and a planar control. (d) *J-V* characteristics of two devices in c.

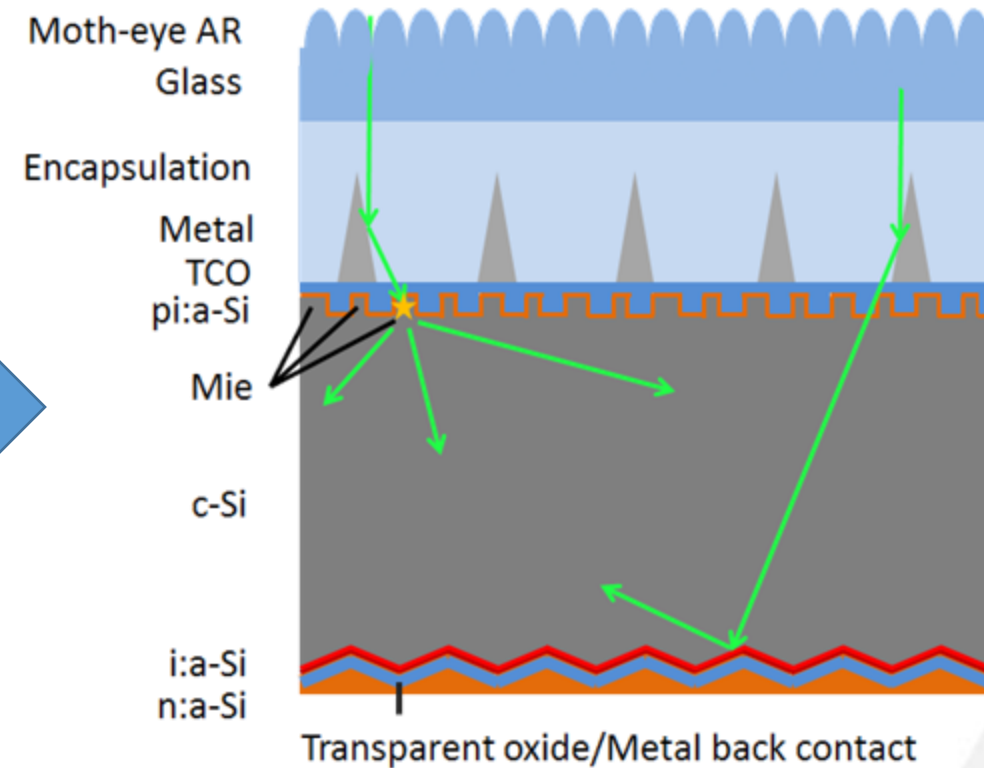
About metaSolar

Building on the Success of Silicon HIT Cells

Current Si Heterojunction Cells



metaSOLAR HIT Cell Design

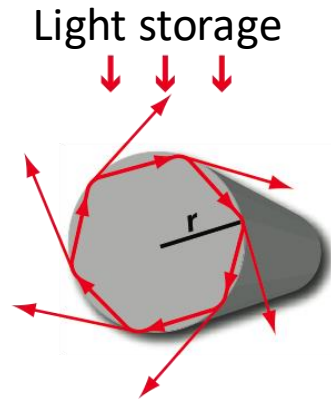


metaSOLAR features:

- Reducing c-Si layer to 50 μ m
- Moth-eye structures as omni-directional anti-reflection coatings on glass
- New transparent metal electrodes
- **Mie scatterers on top surface for anti-reflection and light trapping**

- Adiabatic transition of the refractive index from the superstrate to the substrate
 - Random chemical etching to roughen and texture the substrate surface
 - Nanostructures such as nanowires or nanocones)
- Impedance matching through the design of metal optical nanoantenna.
- **Mie semiconductor resonators to manipulate and trap light**

Resonant Semiconductor Nanostructures



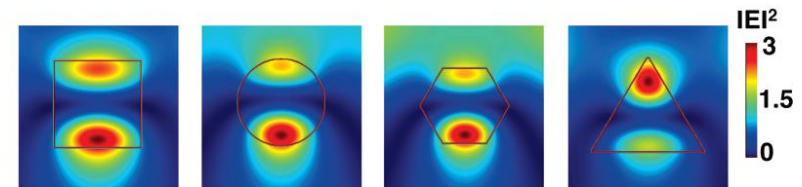
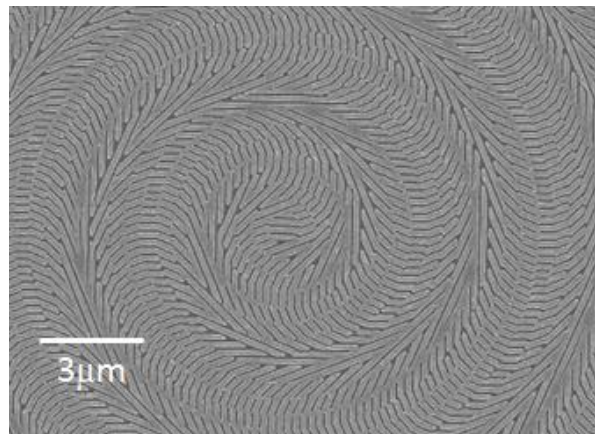
Resonance Condition

$$m\lambda_{eff} = 2\pi r$$

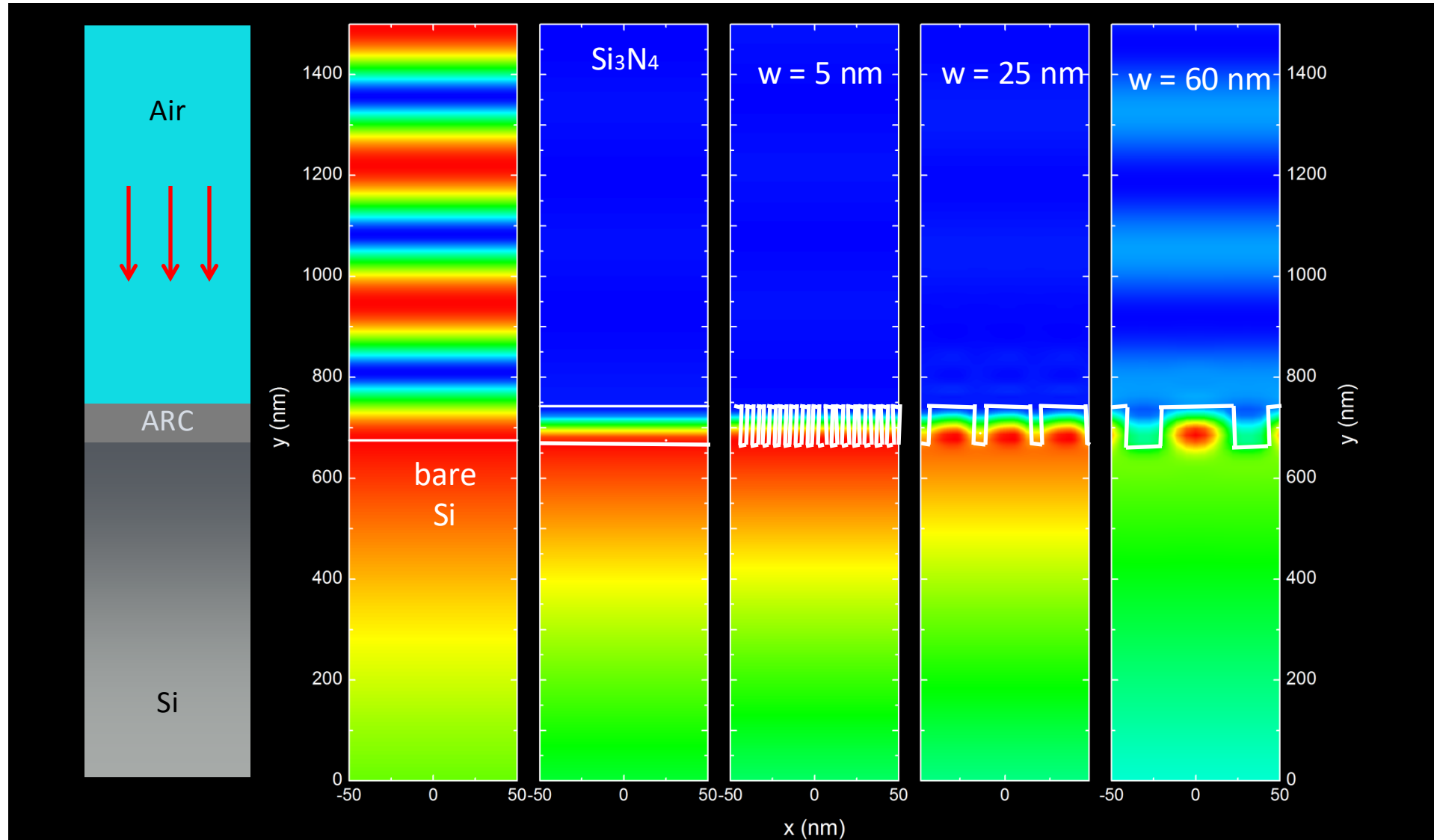
Tuning of light scattering



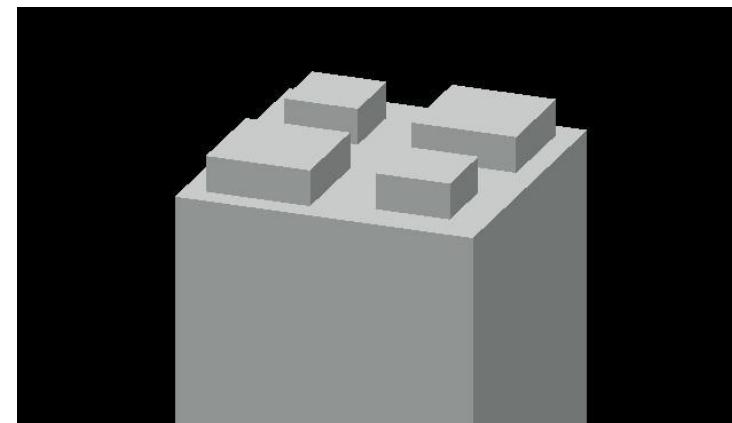
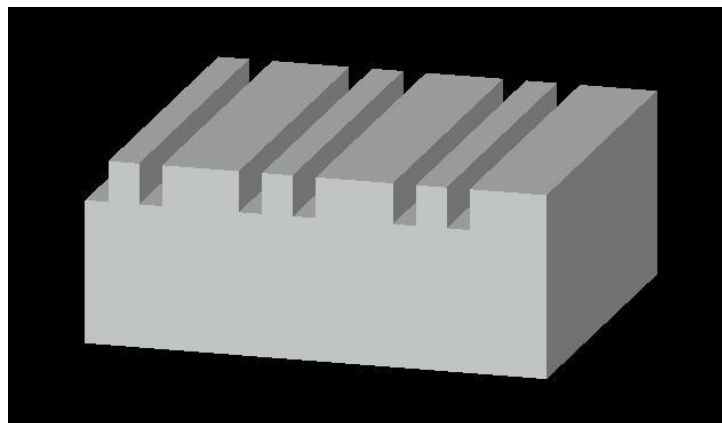
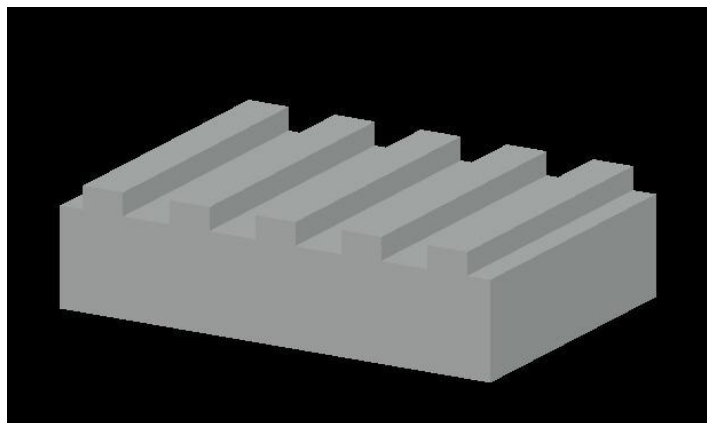
Engineering optical resonance frequency with shape



Transition from a Non-resonant to a Resonant AR Coating

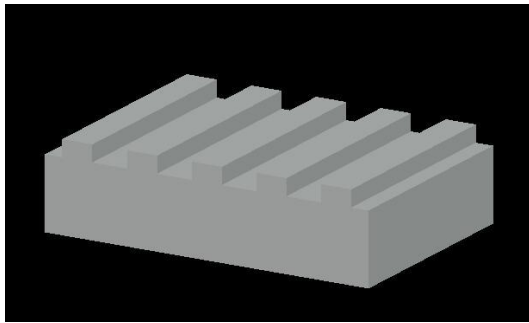


Semiconductor AR Structures

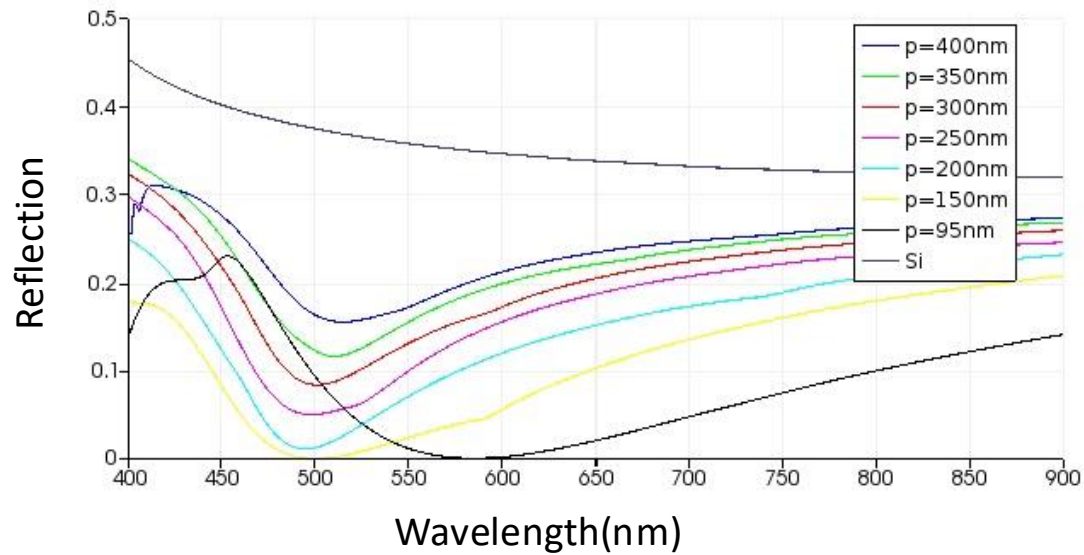


Nanowire AR Coatings

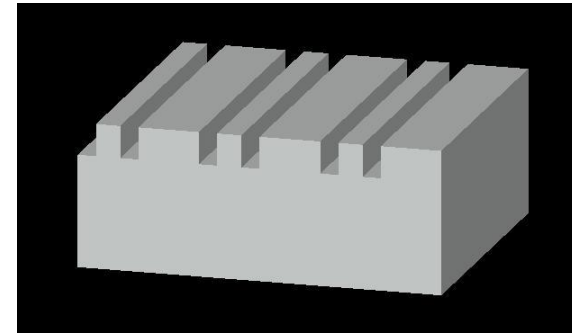
Monomodal



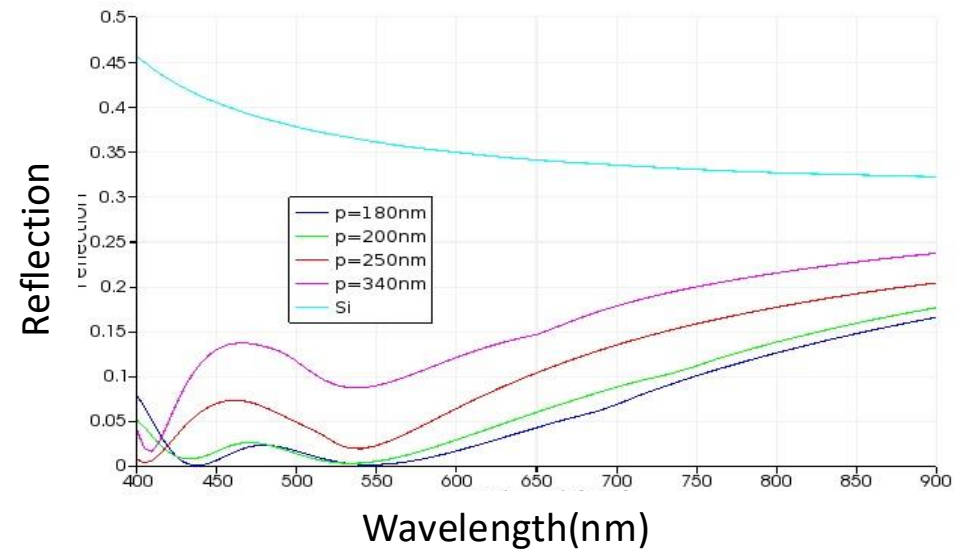
$w = 70\text{nm}$, $t=70\text{nm}$



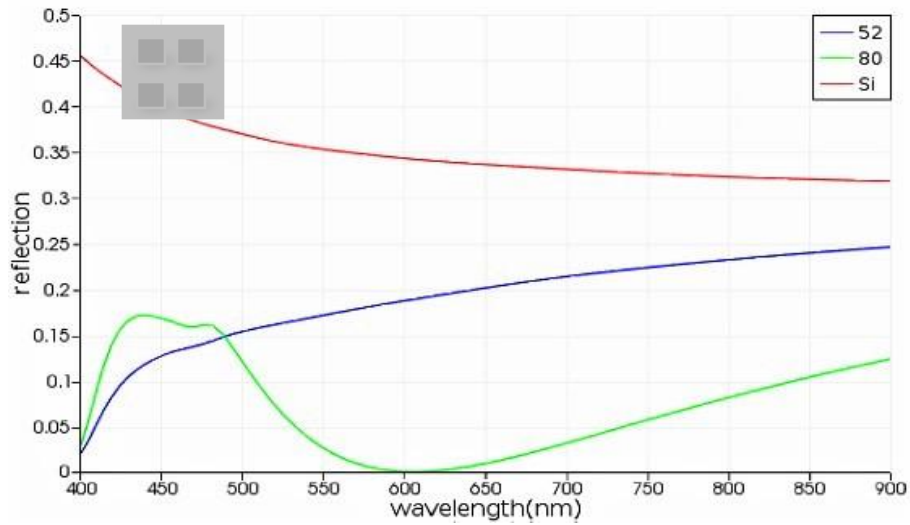
Bimodal



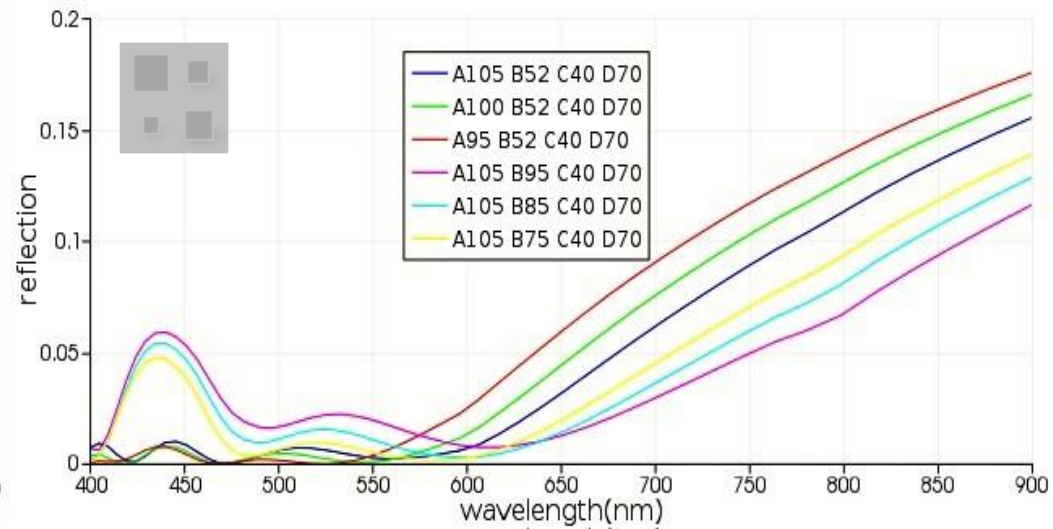
$w_1 = 40\text{nm}$, $w_2=80\text{nm}$, $t=70\text{nm}$



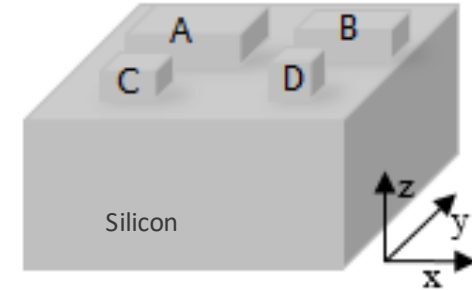
Nanopillar AR Coatings



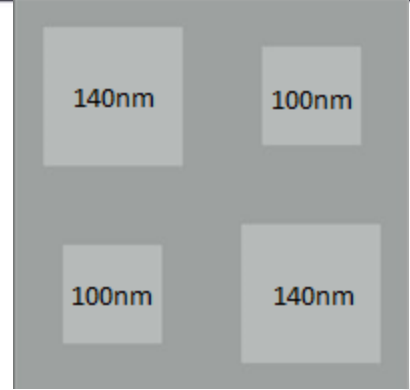
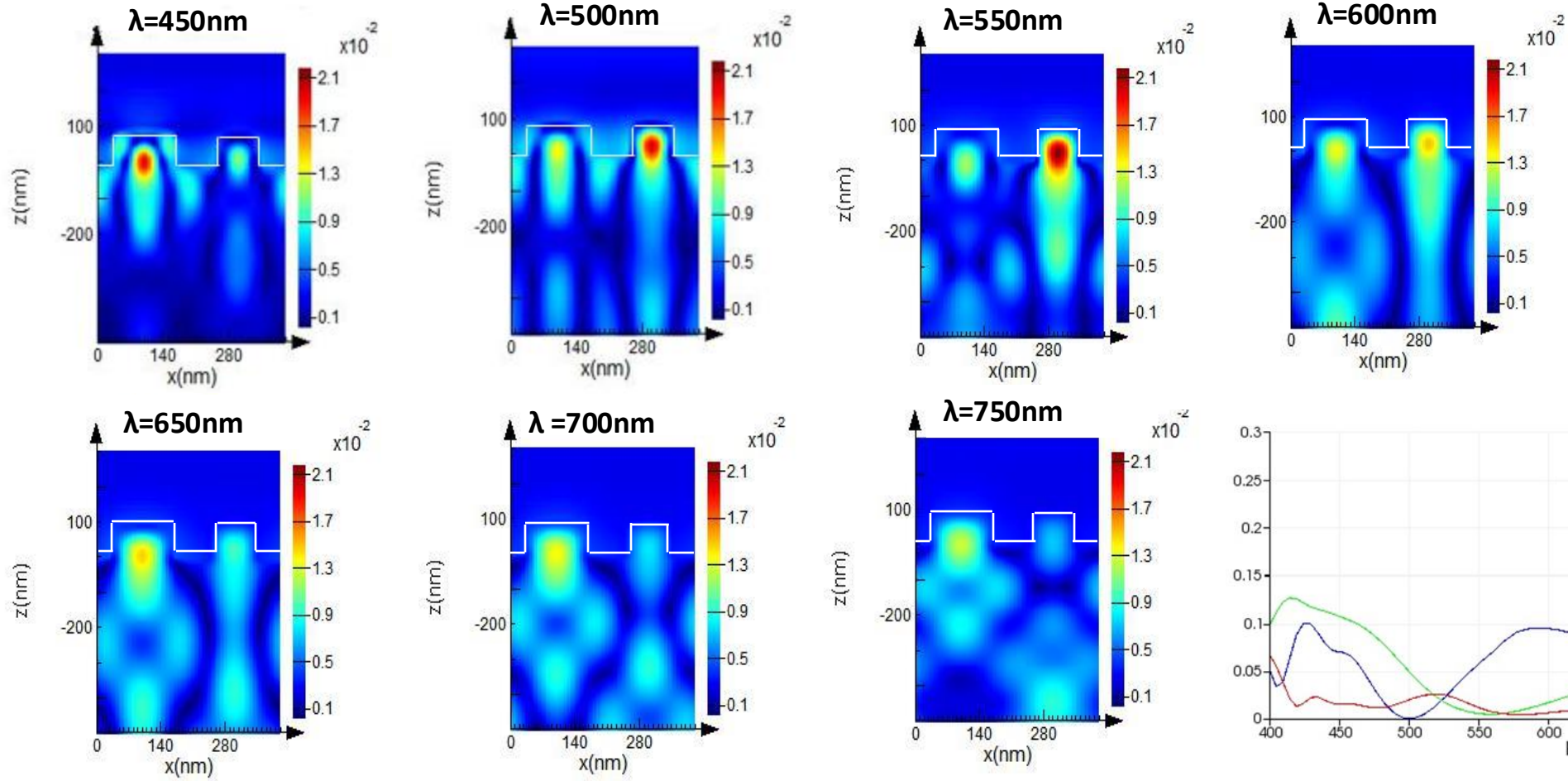
(a) Simulated reflection from the structure shown in the inset for two different pillar sizes 52nm(blue) and 80nm(green). Reflection of bared silicon is shown as reference(red). The unit cell periodicity is 217 nm.



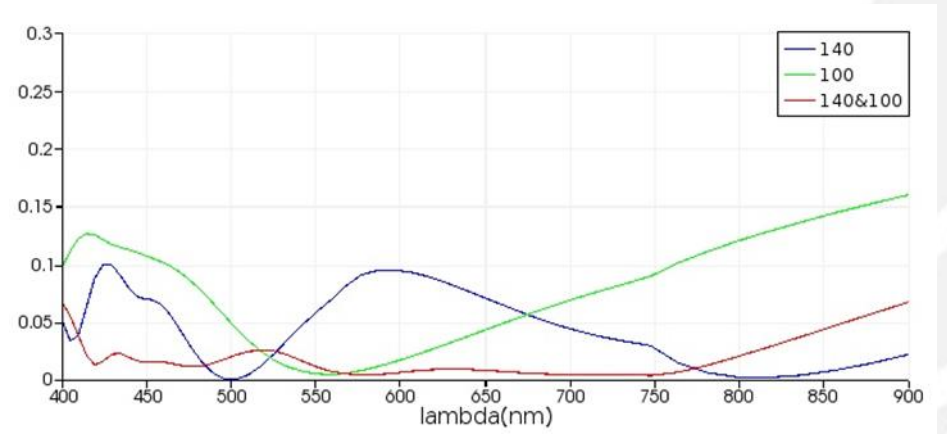
(b) Reflection spectra for four pillars(ABCD) with different width. The unit cell periodicity is 217nm. Insets are the view of the structure from XY plane.



Nanopillar Field Distributions



XY plane 400x400nm



Manufacturing

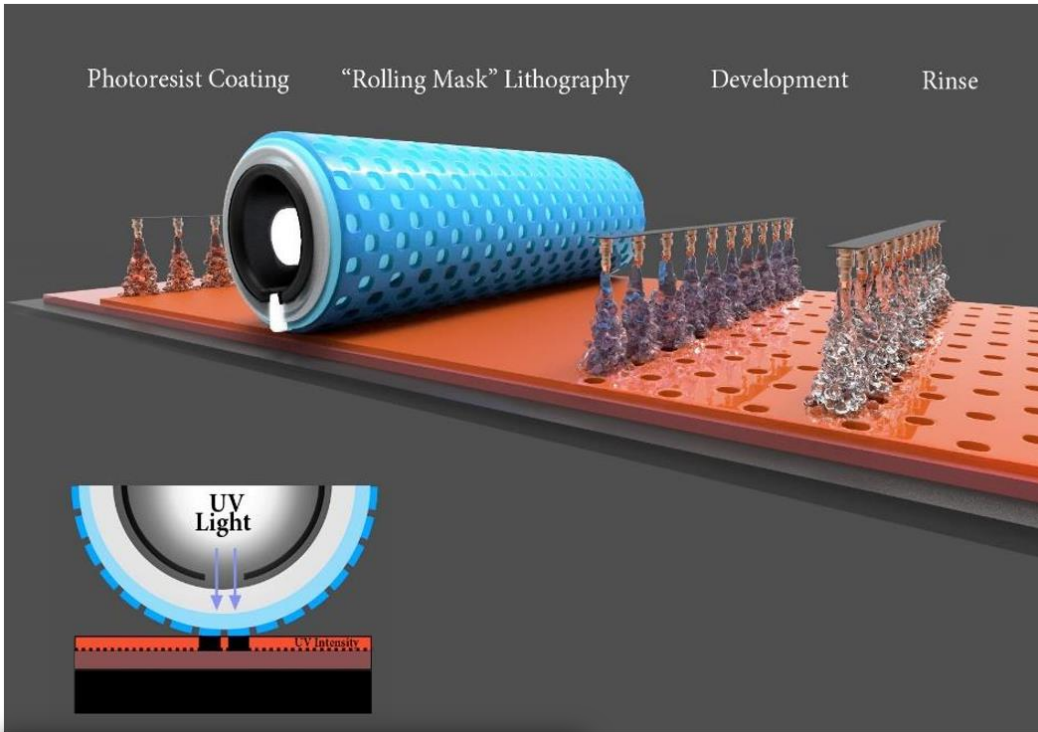
Rolling Mask Lithography

Three frogs are sitting on a log.

One decides to jump.

How many are left?

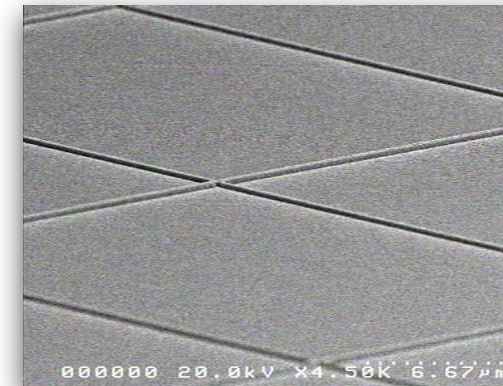
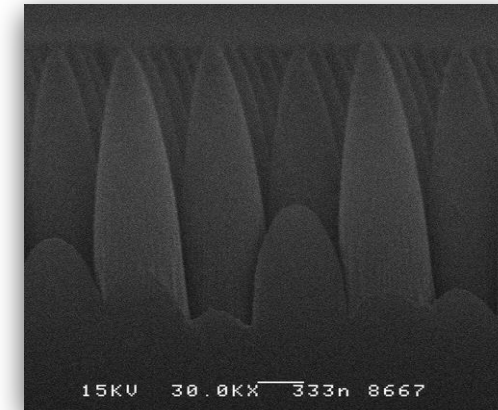
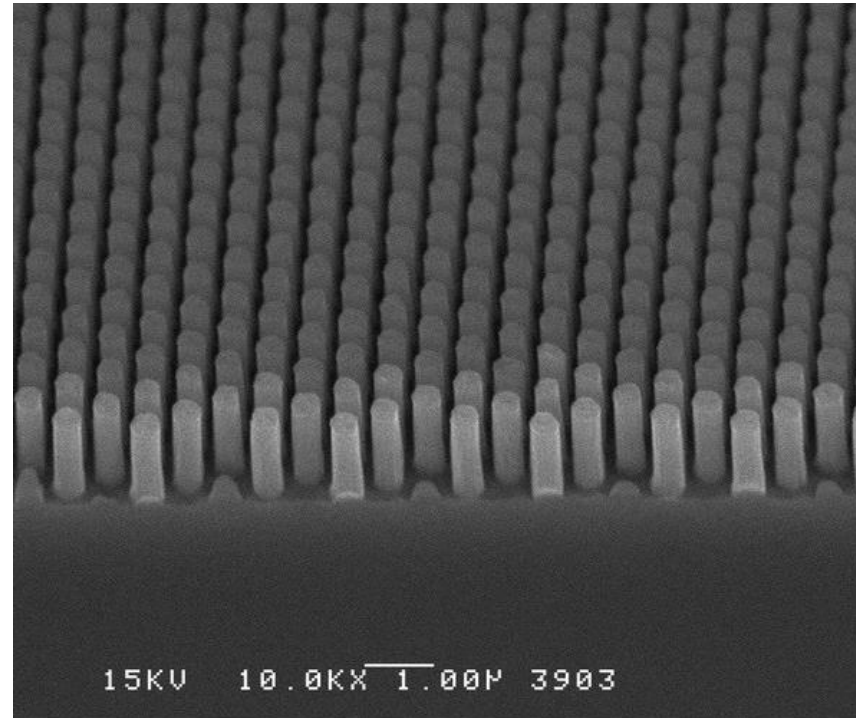
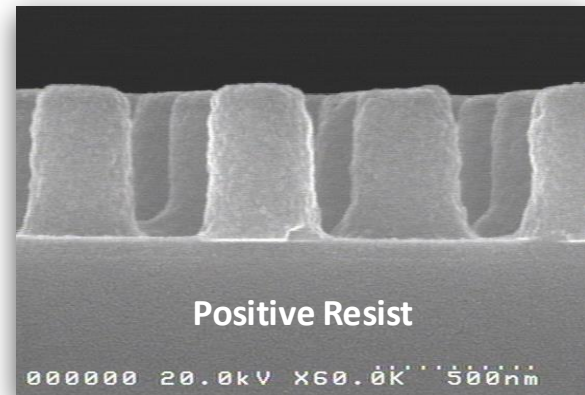
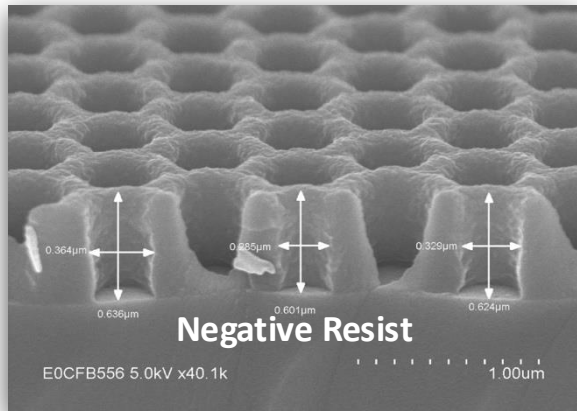
Rolling Mask Lithography - RML[®]



- "Rolling Mask Lithography" (RML[®]) - low cost, high resolution and large area nanopatterning
- Any substrate material (glass, semiconductors, flexible polymer, metal or glass films)
- Scale: up to 1m x 0.3 m (2nd Gen) and R2R continuous 1 m wide web (3rd Gen)
- Resolution: down to 150nm (2nd- Gen); 50 nm (3rd-Gen)
- Inexpensive (<\$1M/tool) versus competition
- Throughput: up to 40m²/h (3rd-Gen)
- Cost target: \$5/m² (3rd-Gen)
- Growing IP portfolio: 22 patent families and 11 granted families



Examples of nanostructures





Thank You

May thanks to:

Owen Mao

Mark Brongersma

NSERC